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Dielectric properties of biphenyl

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Abstract. The dielectric constant along the crystallographic axes was measured. The dielectric anomalies at $T_{\rm I}$ along the *a* and *b* axes show critical exponent $\beta = 0.50 \pm 0.01$ in the incommensurate phase II. At the second phase transition $T_{\rm II}$ no anomaly in dielectric constant was observed.

1. Introduction

In recent years, biphenyl (diphenyl) ($C_{12}H_{10}$, O–O) has been studied intensively (Cailleau *et al* 1979). Two low-temperature incommensurate phases of biphenyl have some unusual features. Phase II, existing for $T_I = 40 \text{ K} > T > T_{II} = 17 \text{ K}$, is one of the few known systems whose order parameter has four components (Cailleau *et al* 1979, Cailleau 1986, Toledano and Guilluy 1984). This allows the existence of two different incommensurate states A and B, called quilt and stripe like. In recent work (Golzhauser *et al* 1989) it was shown that phase II is stripe like. In the present work we report a dielectric study of biphenyl. We show that dielectric anomalies along the *a* and *b* axes at around 40 K have a critical exponent $\beta = 0.50 \pm 0.01$.

2. Experimental procedure

Single crystals of biphenyl were grown from the melt. Samples were cut normal to the a, b and c axes (Charbonneau and Delugeard 1976). The homogeneity of the samples was controlled using a polarising microscope. The capacity of the samples, with silver paste electrodes, was measured with a GR 1616 capacitance bridge at 1 kHz. The temperature of the sample was controlled with an Oxford ITC4 instrument, and the temperature was stable to ± 0.1 K.

3. Results

We studied the dielectric constant parallel to the crystallographic a, b and c directions. The results for the b axis are shown in figure 1. The dielectric constant increases on



Figure 1. Dielectric constant ε_b as a function of the temperature.

Figure 2. Double-logarithmic plot of the dielectric anomaly of the *b* axis below T_1 for biphenyl.

approaching T_{I} at 40 K from higher temperatures and is temperature independent below 40 K; it shows no change on going through T_{II} . The anomaly in ε_b is determined by extrapolating the linear high-temperature behaviour to below T_{I} and taking the difference $\Delta \varepsilon_b$ with respect to the measured values. An isotropic coupling modifies the dependence (Unruh and Stromich 1981)

$$\varepsilon = 1/(\varepsilon_0 + \eta |Q|^2)$$

so that, below $T_{\rm I}$, ε behaves linearly because $|Q|^2 \propto (T_{\rm I} - T)^{2\beta}$. Figure 2 shows that such a relation holds with an exponent β of 0.50 ± 0.01 . The dielectric constant along the *a* axis has almost the same value as along the *b* axis and gives the same critical exponent. A similar behaviour was observed for Rb₂ZnCl₄ and K₂SeO₄ by Unruh and Stromich (1981) and Unruh *et al* (1979); only the value for β was smaller.

Figure 3 shows the temperature dependence of ε_c . Below T_1 the dielectric constant is constant. The temperature dependence for $T > T_1$ is unusual.





4. Conclusions

The dielectric anomalies in biphenyl at $T_{\rm I}$ have a critical exponent β of 0.50 along the *a* and *b* axes. The dielectric constant does not show any anomaly at the $T_{\rm II}$ phase transition. The dielectric constant ε_c has an unusual temperature dependence at $T > T_{\rm I}$.

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